onsemi

Hex 3-State Inverting Buffer with Common Enables and LSTTL Compatible Inputs

High-Performance Silicon-Gate CMOS

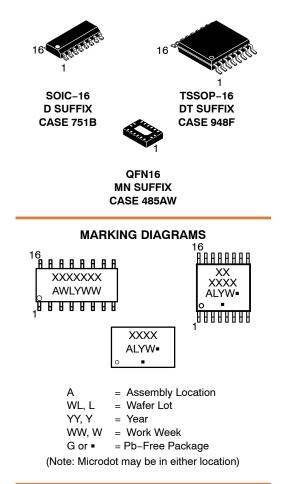
MC74HCT366A

The MC74HCT366A is identical in pinout to the LS366. The device inputs are compatible with standard CMOS or LSTTL outputs.

This device is a high-speed hex buffer with 3-state outputs and two common active-low Output Enables. When either of the enables is high, the buffer outputs are placed into high-impedance states. The HCT366A has inverting outputs.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 µA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 90 FETs or 22.5 Equivalent Gates
- -Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices*



ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

	1•	16	v _{cc}
A0 [2	15	OUTPUT ENABLE 2
Y0 [3	14] A5
A1 [4	13] Y5
Y1 [5	12] A4
A2 [6	11] Y4
Y2 [7	10] A3
GND [8	9] Y3

Figure 1. Pin Assignment

FUNCTION TABLE

	Output		
Enable 1	Enable 2	А	Y
L	L	L	Н
L	L	н	L
н	Х	X	Z
Х	Н	X	Z

X = don't care

Z = high impedance

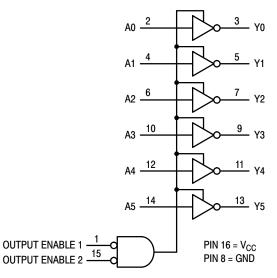


Figure 2. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V
V _{IN}	DC Input Voltage		–0.5 to V _{CC} + 0.5	V
V _{OUT}	DC Output Voltage		–0.5 to V _{CC} + 0.5	V
I _{IN}	DC Input Current, per Pin		±20	mA
I _{OUT}	DC Output Current, per Pin		±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins		±50	mA
I _{IK}	Input Clamp Current (V _{IN} < 0 or V _{IN} > V _{CC})		±20	mA
I _{OK}	Output Clamp Current (V _{OUT} < 0 or V _{OUT} > V _{CC})		±20	mA
T _{STG}	Storage Temperature		65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias		±150	°C
θ_{JA}	Thermal Resistance (Note 1)	SOIC-16 QFN16 TSSOP-16	126 118 159	°C/W
P _D	Power Dissipation in Still Air at 25°C	SOIC-16 QFN16 TSSOP-16	995 1062 787	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating C	xygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V_{ESD}	ESD Withstand Voltage (Note 2)	Human Body Model Charged Device Model	> 2000 N/A	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 Measured with minimum pad spacing on an FR4 board, using 76 mm-by-114 mm, 2-ounce copper trace no air flow per JESD51-7.
HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	6.0	V
V _{in} , V _{out}	DC Input, Output Voltage (Note 3)	0	V _{CC}	V
T _A	Operating Free-Air Temperature	55	+125	°C
t _r , t _f	Input Rise or Fall Time $V_{CC} = 2.0 V$ $V_{CC} = 3.0 V$ $V_{CC} = 4.5 V$ $V_{CC} = 6.0 V$	0 0 0	1000 600 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

3. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC} V	–55 to 25°C	≤ 85 ° C	≤125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$\begin{array}{l} V_{out} = V_{CC} - 0.1 \ V \\ I_{out} \leq 20 \ \mu A \end{array}$	4.5 to 5.5	2.0	2.0	2.0	V
V _{IL}	Maximum Low-Level Input Voltage	$\begin{array}{l} V_{out} = 0.1 \ V \\ I_{out} \leq 20 \ \mu A \end{array}$	4.5 to 5.5	0.80	0.80	0.80	V
V _{OH}	Minimum High-Level Output Voltage		2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\begin{array}{ll} V_{in} = V_{IH} & \begin{array}{ll} I_{out} \\ I_{out} \\ I_{out} \\ I_{out} \\ \leq 6.0 \text{ mA} \\ I_{out} \\ \leq 7.8 \text{ mA} \end{array}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low-Level Output Voltage		2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{array}{l l} V_{in} = V_{IL} & \left \begin{matrix} I_{out} \end{matrix} \right \leq 3.6 \text{ mA} \\ \left \begin{matrix} I_{out} \end{matrix} \right \leq 6.0 \text{ mA} \\ \left \begin{matrix} I_{out} \end{matrix} \right \leq 7.8 \text{ mA} \end{array}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Cur- rent	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μΑ
I _{OZ}	Maximum Three-State Leakage Current	Output in High–Impedance State $V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	6.0	±0.5	±5.0	±10	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $I_{out} = 0 \ \mu A$	6.0	4	40	160	μΑ

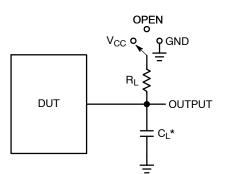
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

			Gu	aranteed Li	mit	
Symbol	Parameter	V _{CC} V	–55 to 25°C	≤ 85°C	≤125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 3 and 4)	2.0 3.0 4.5 6.0	120 60 24 20	150 75 30 26	180 90 36 31	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	220 110 44 37	275 140 55 47	330 170 66 56	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	220 110 44 37	275 140 55 47	330 170 66 56	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 3 and 4)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C _{in}	Maximum Input Capacitance	-	10	10	10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	-	15	15	15	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Buffer)*	60	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. *Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.



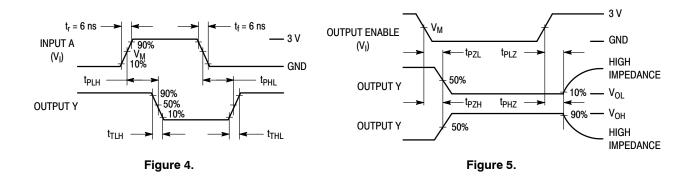
Test	Switch Position	CL	RL
t _{PLH} / t _{PHL}	Open	50 pF	1 kΩ
t _{PLZ} / t _{PZL}	V _{CC}		
t _{PHZ} / t _{PZH}	GND		

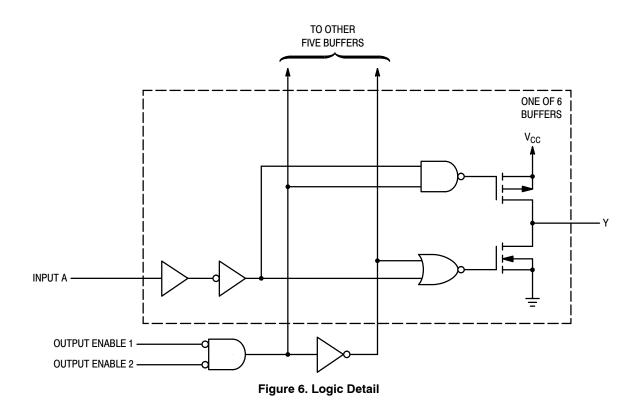
 $^{*}C_{L}$ Includes probe and jig capacitance

Figure 3. Test Circuit



 $(V_{I} = 0 \text{ to } 3 \text{ V}, V_{M} = 1.3 \text{ V})$



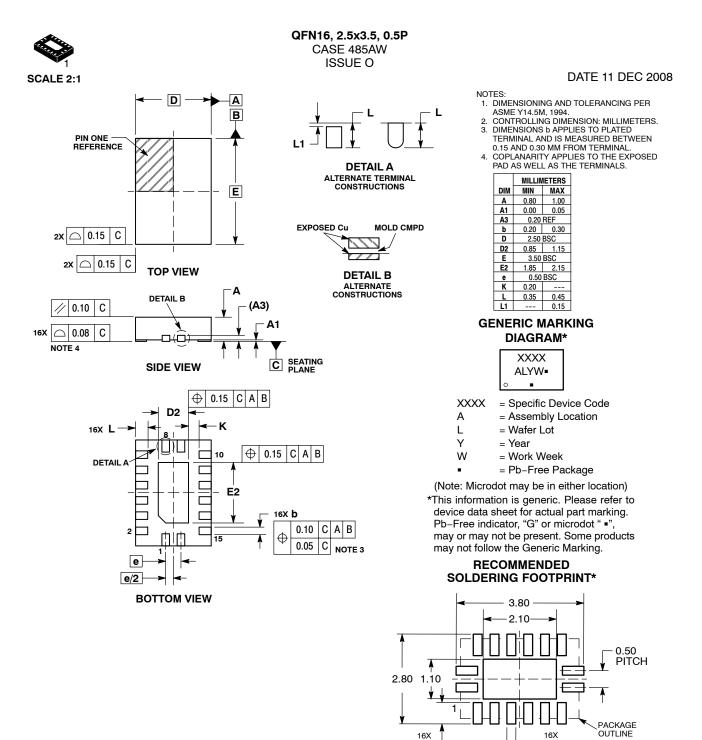


ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MC74HCT366ADR2G	HCT366AG	SOIC-16	2500 / Tape & Reel
MC74HCT366ADTR2G	HCT 366A	TSSOP-16	2500 / Tape & Reel
MC74HCT366ADTR2G-Q*	HCT 366A	TSSOP-16	2500 / Tape & Reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*–Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS



DIMENSIONS: MILLIMETERS *For additional information on our Pb-Free strategy and soldering

0.30

details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

0.60



MILLIMETERS

NOM

1.55

0.18

1.37

0.42

0.22

9.90 BSC

MIN

1.35

0.10

1.25

0.35

0.19

DIM

А

Α1

A2

b

С

D

SOIC-16 9.90x3.90x1.37 1.27P CASE 751B ISSUE M

DATE 18 OCT 2024

MAX

1.75

0.25

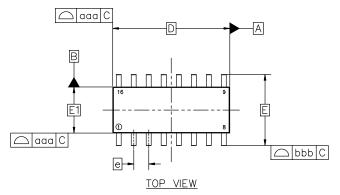
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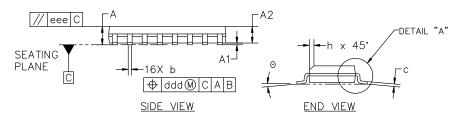
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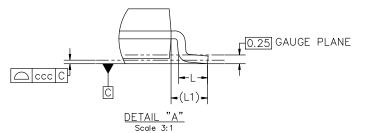
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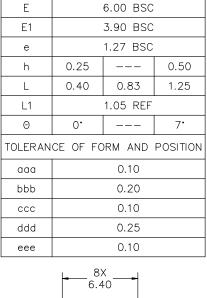
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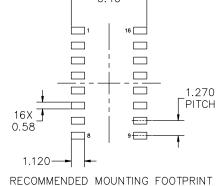
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE & DIMENSION AT MAXIMUM MATERIAL CONDITION.











*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE onsemi SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D

DOCUMENT NUMBER:	98ASB42566B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED	
DESCRIPTION:	SOIC-16 9.90X3.90X1.37 1	.27P	PAGE 1 OF 2

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DATE 18 OCT 2024

GENERIC MARKING DIAGRAM*

16	A	H	A.	- A	- A	A	A.	Æ
		XX)						
		XX	XX	XX	XX	XX)	XX	x
	0			NĽ				
1	H	Н	Н	Н	Н	Н	Н	Ъ

XXXXX = Specific Device Code

A = Assembly Location

- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package

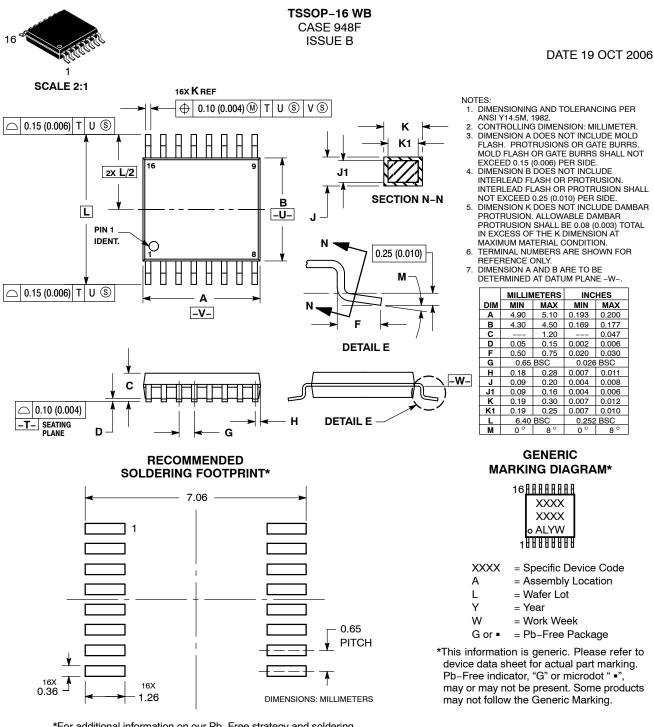
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:		STYLE 2:		STYLE 3:	c	STYLE 4:	
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE #1
2.		2.	ANODE	2.	BASE, #1	2.	,
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	,
	EMITTER		CATHODE		COLLECTOR, #2		COLLECTOR, #3
5. 6.		5. 6.	NO CONNECTION	5. 6.	BASE. #2	5. 6.	COLLECTOR, #3
0. 7.		0. 7.		7.	- ,	7.	
8.		8.	CATHODE	8.		8.	,
	BASE	9.	CATHODE		COLLECTOR, #2	9.	,
10.	EMITTER	•.	ANODE		BASE, #3	10.	- ,
	NO CONNECTION	11.	NO CONNECTION		EMITTER, #3	11.	
	EMITTER	12.	CATHODE		COLLECTOR, #3	12.	
	BASE	13.	CATHODE	13.		13.	, .
14.		14.	NO CONNECTION		BASE, #4	14.	
15.	EMITTER	15.	ANODE	15.		15.	BASE, #1
16.		16.	CATHODE	16.		16.	EMITTER, #1
STYLE 5:		STYLE 6:		STYLE 7:			
STYLE 5: PIN 1.	DRAIN, DYE #1	STYLE 6: PIN 1.	CATHODE	STYLE 7: PIN 1.	SOURCE N-CH		
	DRAIN, DYE #1 DRAIN, #1		CATHODE CATHODE	••••	SOURCE N-CH COMMON DRAIN (OUTPUT)	1	
PIN 1.	,	PIN 1.		PIN 1.			
PIN 1. 2.	DRAIN, #1	PIN 1. 2.	CATHODE	PIN 1. 2.	COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT		
PIN 1. 2. 3.	DRAIN, #1 DRAIN, #2	PIN 1. 2. 3.	CATHODE CATHODE	PIN 1. 2. 3.	COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT		
PIN 1. 2. 3. 4.	DRAIN, #1 DRAIN, #2 DRAIN, #2	PIN 1. 2. 3. 4.	CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH		
PIN 1. 2. 3. 4. 5.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3	PIN 1. 2. 3. 4. 5.	CATHODE CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5.	COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT GATE P-CH COMMON DRAIN (OUTPUT		
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